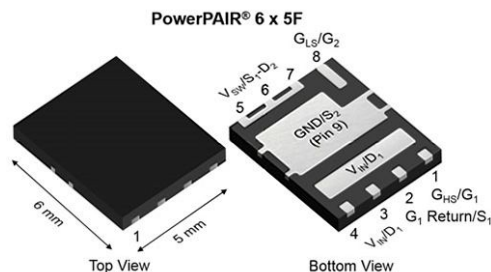


Dual N-Channel 30 V (D-S) MOSFET with Schottky Diode



FEATURES

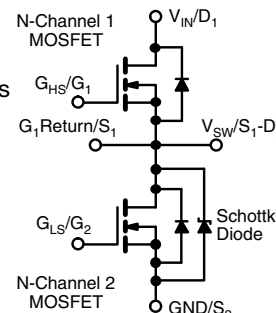
- TrenchFET® Gen IV power MOSFET
- SkyFET® low-side MOSFET with integrated Schottky
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- CPU core power
- Computer / server peripherals
- POL
- Synchronous buck converter
- Telecom DC/DC



PRODUCT SUMMARY		
	CHANNEL-1	CHANNEL-2
V_{DS} (V)	30	30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.00380	0.00117
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.00530	0.00158
Q_g typ. (nC)	11	46
I_D (A) ^a	60	60
Configuration	Dual	

ORDERING INFORMATION		
Package	PowerPAIR 6 x 5F	
Lead (Pb)-free and halogen-free	SiZF906ADT-T1-GE3	

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	CHANNEL-1	CHANNEL-2	UNIT	
Drain-source voltage		V _{DS}	30		V	
Gate-source voltage		V _{GS}	+20, -16			
Continuous drain current (T _J = 150 °C)	T _C = 25 °C	I _D	60 ^a	60 ^a	A	
	T _C = 70 °C		60 ^a	60 ^a		
	T _A = 25 °C		27 ^{b, c}	52 ^{b, c}		
	T _A = 70 °C		21.7 ^{b, c}	41 ^{b, c}		
Pulsed drain current (t = 100 μs)		I _{DM}	80	100		
Continuous source-drain diode current	T _C = 25 °C	I _S	31.6	60 ^a		
	T _A = 25 °C		3.7 ^{b, c}	4.1 ^{b, c}		
Single pulse avalanche current		L = 0.1 mH	I _{AS}	18		19
Single pulse avalanche energy			E _{AS}	16	18	mJ
Maximum power dissipation	T _C = 25 °C	P _D	38	83	W	
	T _C = 70 °C		24	53		
	T _A = 25 °C		4.5 ^{b, c}	5 ^{b, c}		
	T _A = 70 °C		2.9 ^{b, c}	3.2 ^{b, c}		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150		°C	
Soldering recommendations (peak temperature) ^{d, e}			260			

THERMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL	CHANNEL-1		CHANNEL-2		UNIT
			TYP.	MAX.	TYP.	MAX.	
Maximum junction-to-ambient ^{b, f}	$t \leq 10$ s	R_{thJA}	22	28	20	25	°C/W
Maximum junction-to-case (source)	Steady state	R_{thJC}	2.6	3.3	1.2	1.5	

Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 60 °C/W for channel-1 and 60 °C/W for channel-2



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	Ch-1	30	-	-	V	
			Ch-2	30	-	-		
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1.1	-	2.2		
			Ch-2	1.1	-	2.2		
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20 V, -16 V	Ch-1	-	-	± 100	nA	
			Ch-2	-	-	± 100		
Zero Gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1	-	-	1	μA	
			Ch-2	-	50	250		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	Ch-1	-	-	5		
			Ch-2	-	300	3000		
On-state drain current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	Ch-1	20	-	-	A	
			Ch-2	20	-	-		
Drain-source on-state resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A	Ch-1	-	0.00300	0.00380	Ω	
		V _{GS} = 10 V, I _D = 20 A	Ch-2	-	0.00090	0.00117		
		V _{GS} = 4.5 V, I _D = 10 A	Ch-1	-	0.00400	0.00530		
		V _{GS} = 4.5 V, I _D = 15 A	Ch-2	-	0.00120	0.00158		
Forward transconductance ^b	g _{fs}	V _{DS} = 10 V, I _D = 15 A	Ch-1	-	130	-	S	
		V _{DS} = 10 V, I _D = 20 A	Ch-2		130	-		
Dynamic ^a								
Input capacitance	C _{iss}	Channel-1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz Channel-2 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1	-	2000	-	pF	
			Ch-2	-	8200	-		
Output capacitance	C _{oss}		Ch-1	-	680	-		
			Ch-2	-	3700	-		
Reverse transfer capacitance	C _{rss}		Ch-1	-	50	-		
			Ch-2	-	260	-		
C _{rss} /C _{iss} ratio			Ch-1	-	0.025	0.050		
			Ch-2		0.033	0.070		
Total gate charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A	Ch-1	-	24.5	49	nC	
			Ch-2	-	100	200		
		Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A	Ch-1		11	22		
			Ch-2	-	46	92		
Gate-source charge	Q _{gs}	Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A	Ch-1	-	5.1	-		
			Ch-2	-	17.1	-		
Gate-drain charge	Q _{gd}		Ch-1	-	1.3	-		
			Ch-2	-	7.2	-		
Output charge	Q _{oss}	V _{DS} = 15 V, V _{GS} = 0 V	Ch-1	-	21	-		
			Ch-2	-	96	-		
Gate resistance	R _g	f = 1 MHz	Ch-1	0.2	1	2	Ω	
			Ch-2	0.12	0.6	1.2		



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Dynamic ^a							
Turn-on delay time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	20	40	ns
			Ch-2	-	45	90	
Rise time	t _r		Ch-1	-	80	160	
			Ch-2	-	60	120	
Turn-off delay time	t _{d(off)}	Ch-1	-	20	40		
		Ch-2	-	65	130		
Fall time	t _f	Ch-1	-	40	80		
		Ch-2	-	30	60		
Turn-on delay time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	10	20	
			Ch-2	-	15	30	
Rise time	t _r		Ch-1	-	35	70	
			Ch-2	-	20	40	
Turn-off delay time	t _{d(off)}	Ch-1	-	20	40		
		Ch-2	-	40	80		
Fall time	t _f	Ch-1	-	10	20		
		Ch-2	-	10	20		
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	T _C = 25 °C	Ch-1	-	-	31.6	A
			Ch-2	-	-	60	
Pulse diode forward current ^a	I _{SM}		Ch-1	-	-	80	
			Ch-2	-	-	100	
Body diode voltage	V _{SD}	I _S = 10 A, V _{GS} = 0 V	Ch-1	-	0.8	1.2	V
		I _S = 3 A, V _{GS} = 0 V	Ch-2	-	0.39	0.59	
Body diode reverse recovery time	t _{rr}	Channel-1 I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C	Ch-1	-	35	90	ns
			Ch-2	-	70	140	
Body diode reverse recovery charge	Q _{rr}		Ch-1	-	20	40	nC
			Ch-2	-	105	210	
Reverse recovery fall time	t _a	Channel-2 I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C	Ch-1	-	15	-	ns
			Ch-2	-	37	-	
Reverse recovery rise time	t _b		Ch-1	-	20	-	
			Ch-2	-	33	-	

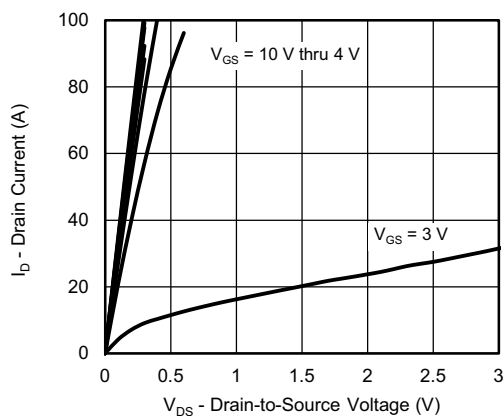
Notes

- a. Guaranteed by design, not subject to production testing
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

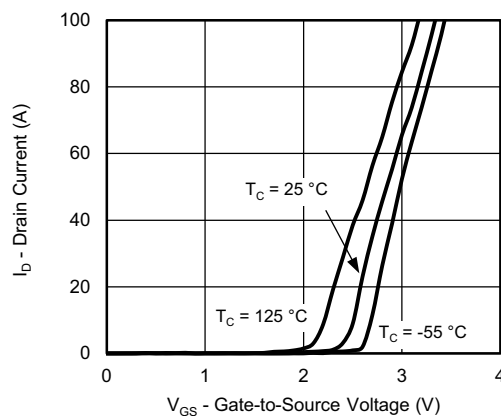
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



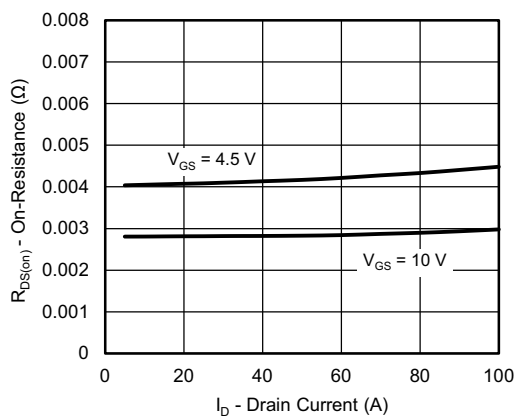
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



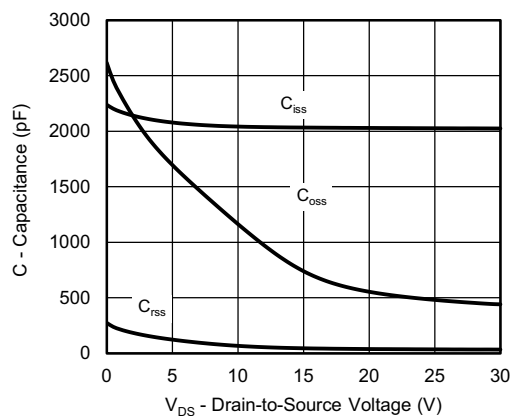
Output Characteristics



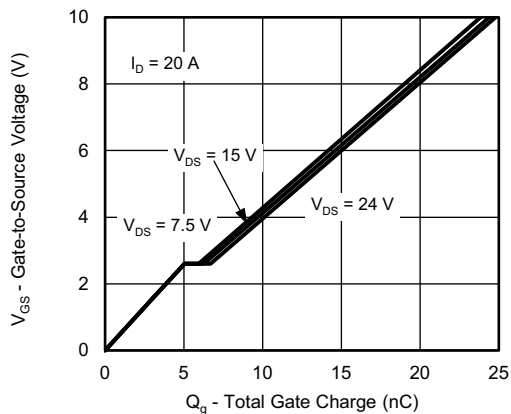
Transfer Characteristics



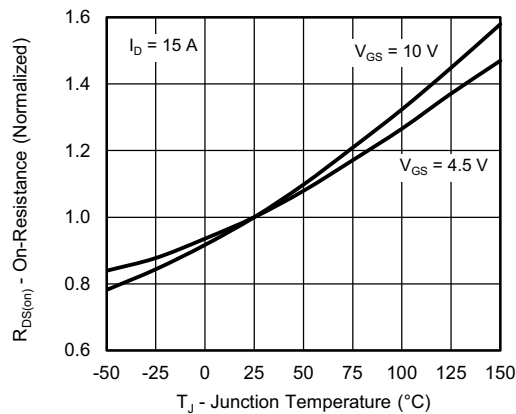
On-Resistance vs. Drain Current



Capacitance



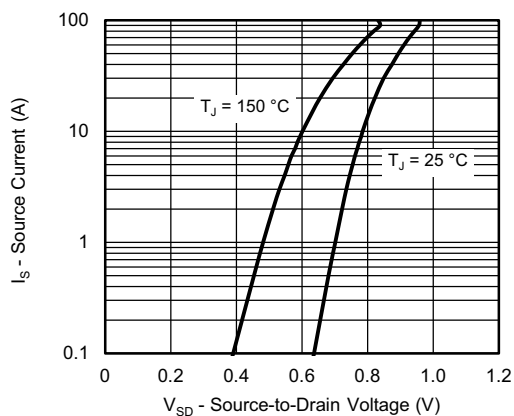
Gate Charge



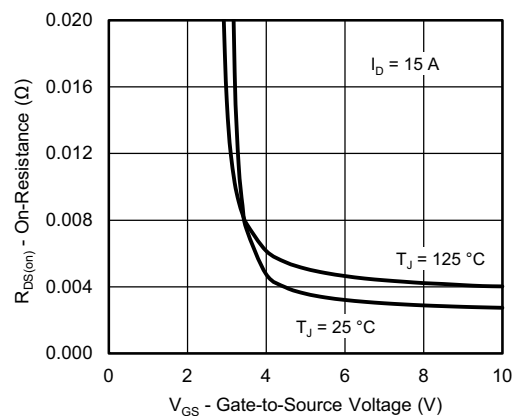
On-Resistance vs. Junction Temperature



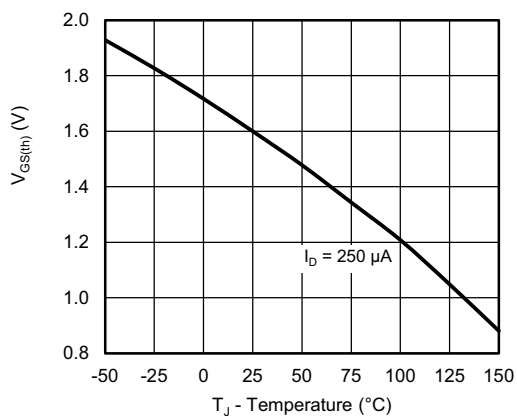
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



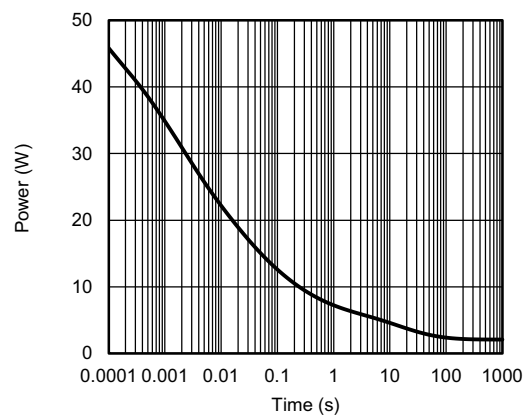
Source-Drain Diode Forward Voltage



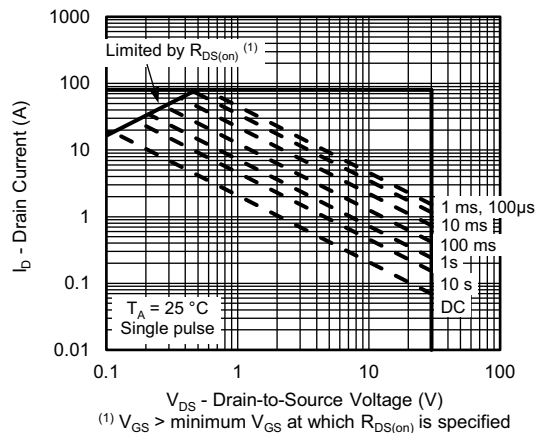
On-Resistance vs. Gate-to-Source Voltage



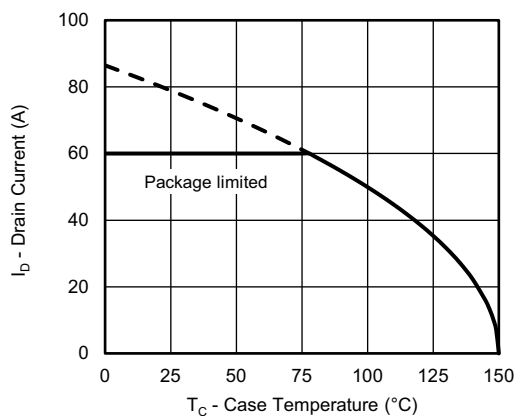
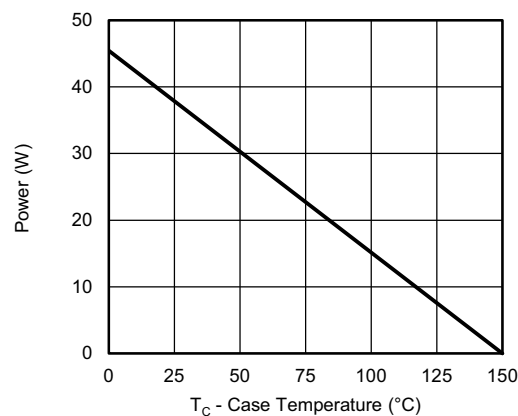
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



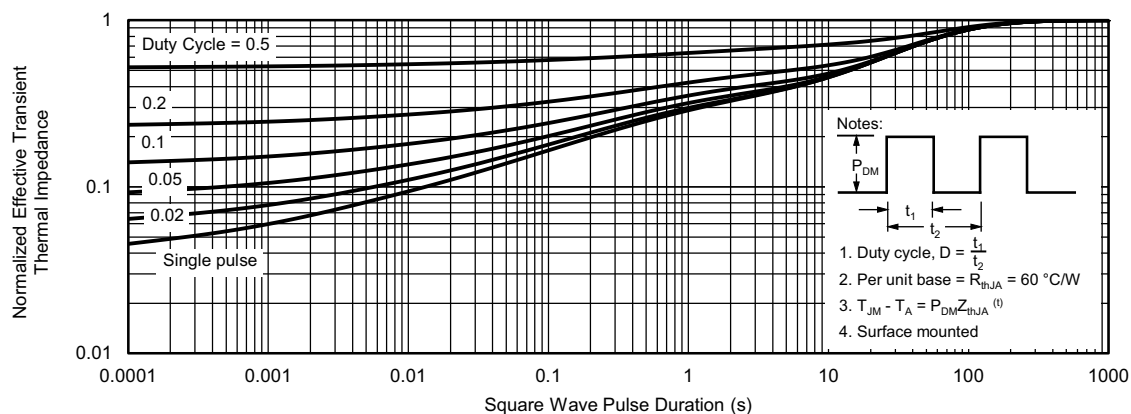
Safe Operating Area, Junction-to-Ambient

CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Case
Note

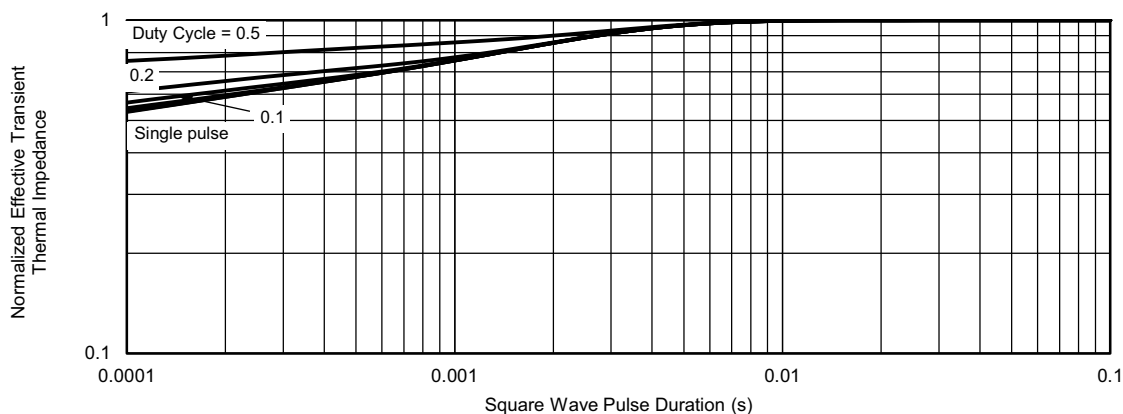
- a. The power dissipation P_D is based on $T_J \text{ max.} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



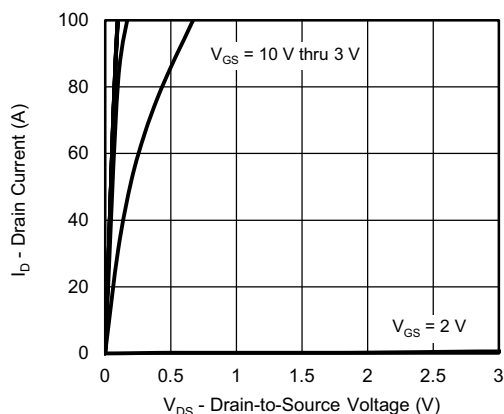
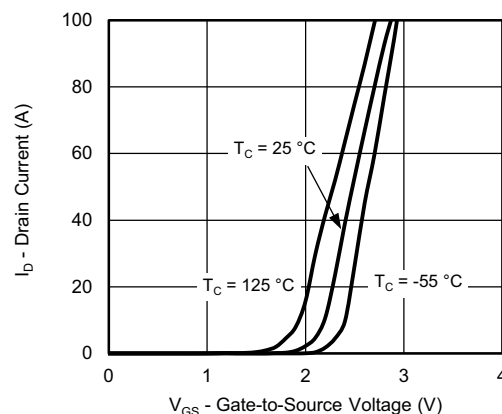
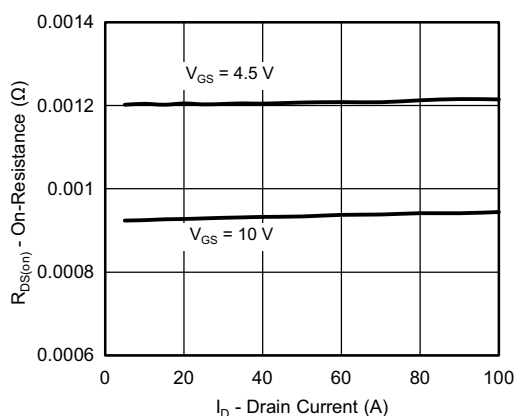
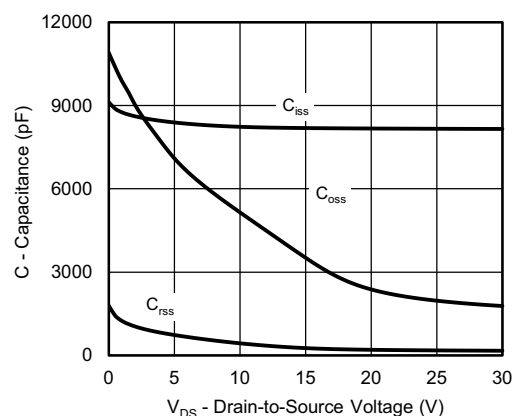
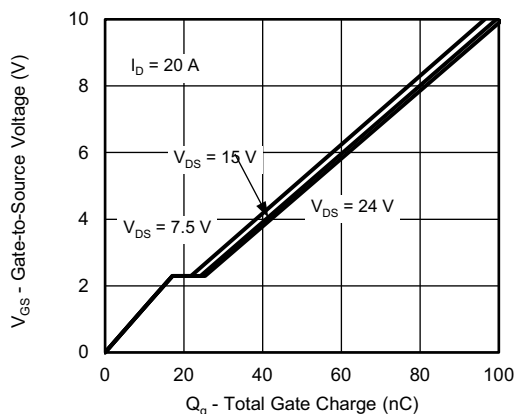
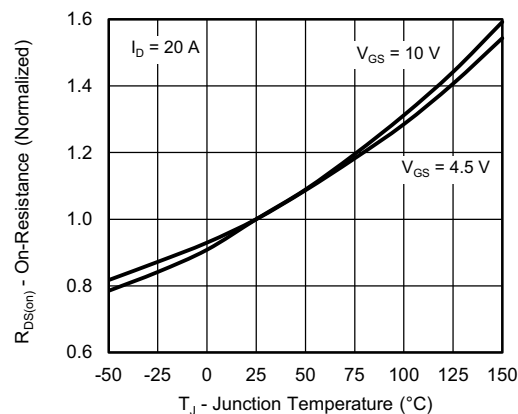
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

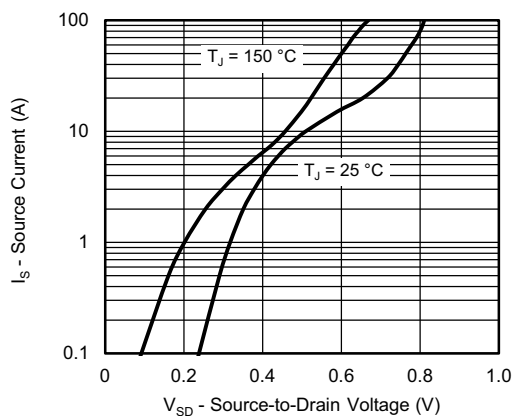


Normalized Thermal Transient Impedance, Junction-to-Case

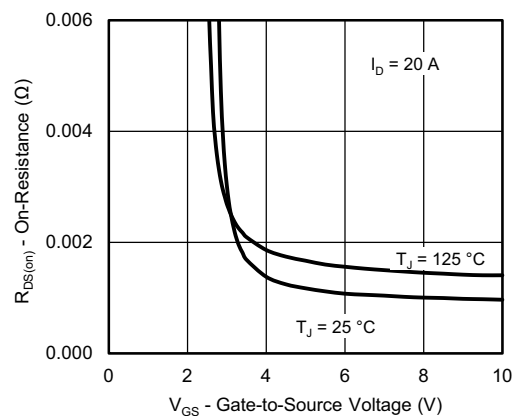
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature



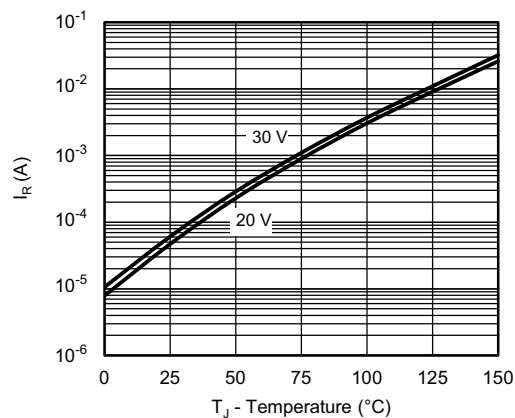
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



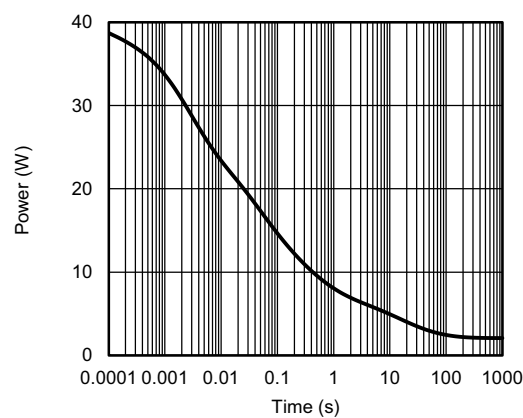
Source-Drain Diode Forward Voltage



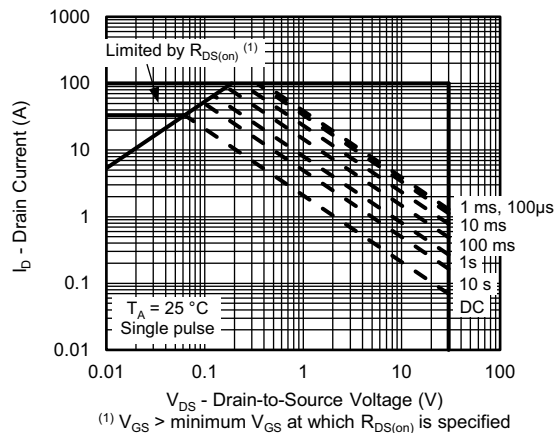
On-Resistance vs. Gate-to-Source Voltage



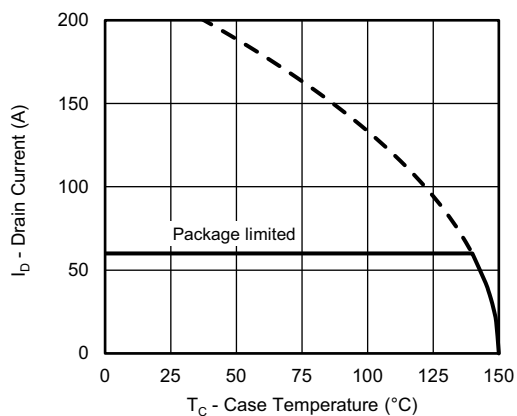
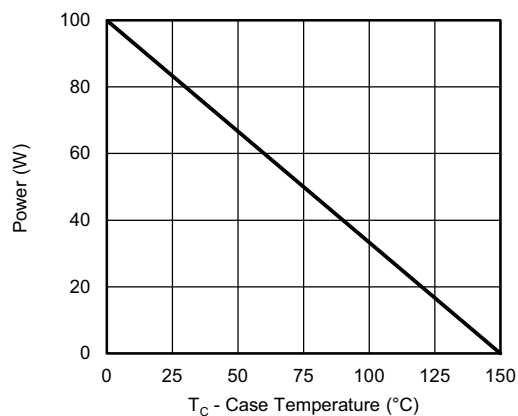
Reverse Current (Schottky)



Single Pulse Power, Junction-to-Ambient



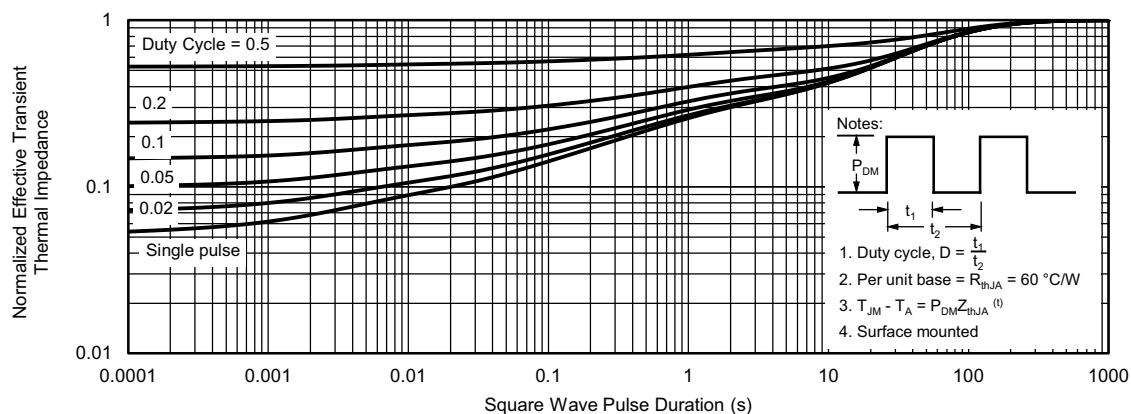
Safe Operating Area, Junction-to-Ambient

CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Case
Note

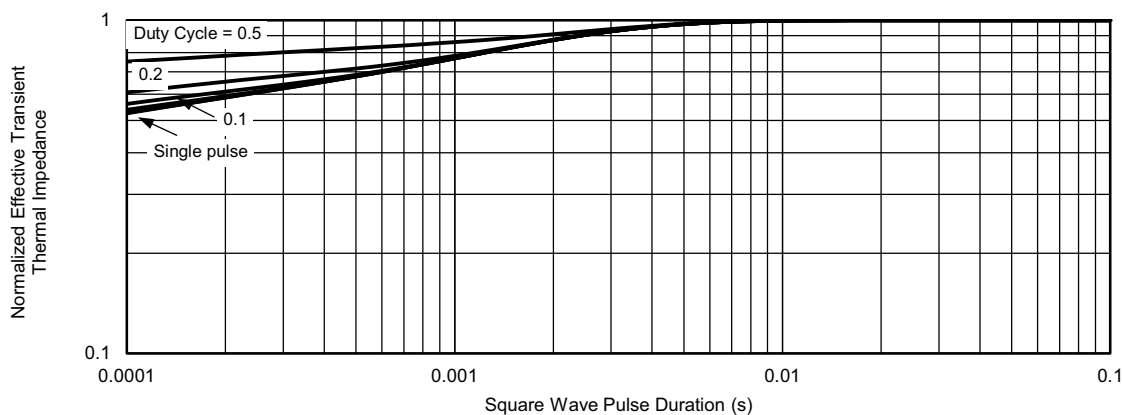
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



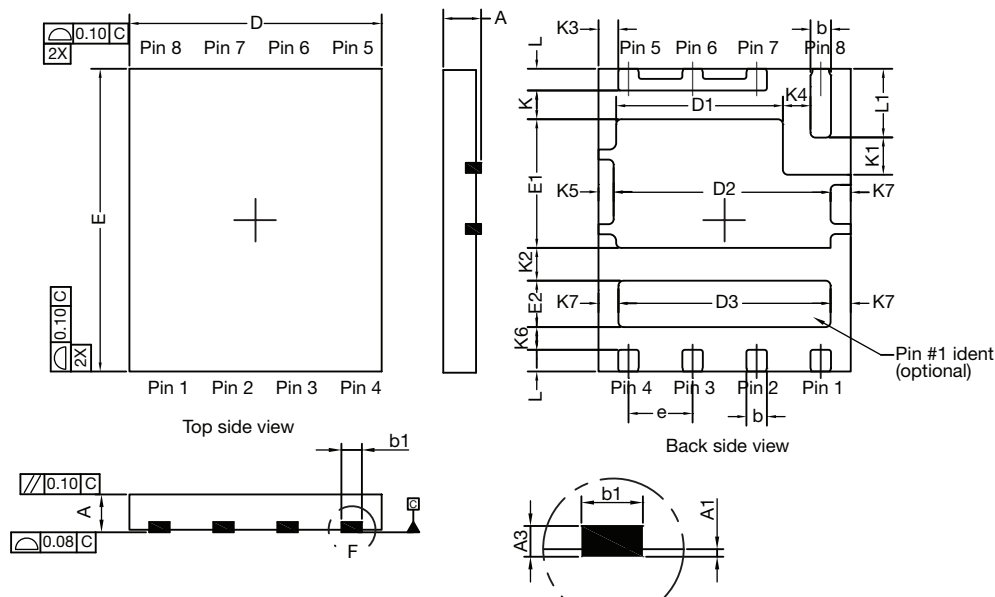
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75695.

Flip PowerPAIR® 6 x 5 BWL Case Outline



DIMENSION	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.032
A1	0.00	-	0.10	0.000	-	0.004
A3	0.15	0.20	0.25	0.006	0.008	0.010
b	0.35	0.41	0.46	0.014	0.016	0.018
b1	0.41 BSC			0.016 BSC		
D	4.90	5.00	5.10	0.193	0.197	0.201
D1	3.26	3.31	3.36	0.128	0.130	0.132
D2	4.20	4.25	4.30	0.165	0.167	0.169
D3	4.15	4.20	4.25	0.163	0.165	0.167
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	2.50	2.55	2.60	0.098	0.100	0.102
E2	0.87	0.92	0.97	0.034	0.036	0.038
e	1.27 BSC			0.050 BSC		
K	0.57 typ.			0.022 typ.		
K1	0.69	0.74	0.79	0.027	0.029	0.031
K2	0.60	0.65	0.70	0.024	0.026	0.028
K3	0.39 BSC			0.015 BSC		
K4	0.50	0.55	0.60	0.020	0.022	0.024
K5	0.25	0.30	0.35	0.010	0.012	0.014
L	0.33	0.43	0.53	0.013	0.017	0.021
L1	1.31	1.36	1.41	0.052	0.054	0.056
ECN: T15-0457-Rev. A, 17-Aug-15						
DWG: 6043						

Note

- Millimeters will govern.



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